

# **PSMN069-100YS**

# N-channel LFPAK 100 V 72.4 m $\Omega$ standard level MOSFET

Rev. 02 — 25 October 2010

**Product data sheet** 

## 1. Product profile

## 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

## 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I <sub>D</sub>	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1	-	-	17	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	56	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 100 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	-	130	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 13}$	-	56.6	72.4	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$	-	4.8	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	14	-	nC
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 17 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	-	24	mJ

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN069-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{ or } \text{ or }  o$	-	12	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	-	17	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	68	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	56	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	17	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	68	Α
Avalanche r	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 17 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	24	mJ

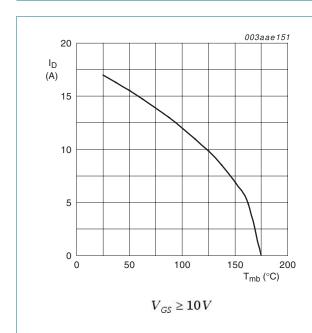


Fig 1. Continuous drain current as a function of mounting base temperature

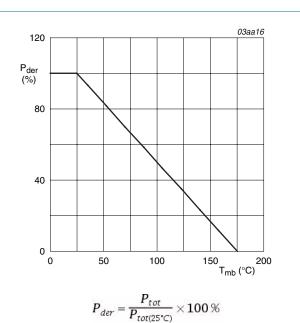
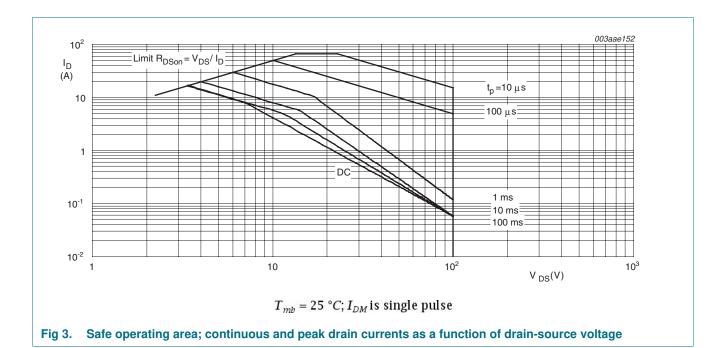


Fig 2. Normalized total power dissipation as a function of mounting base temperature



## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.6	2.7	K/W

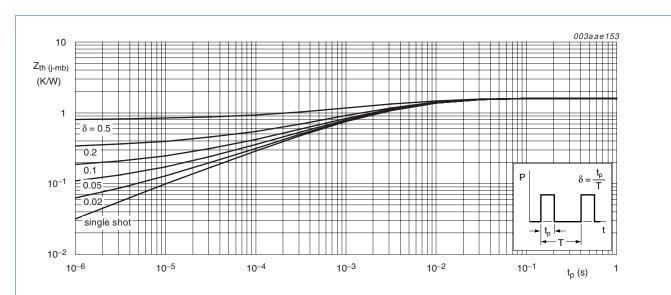


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10	1.2	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2.3	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	4.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.07	2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	130	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	149	202.7	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	56.6	72.4	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.67	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	$I_D = 15 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	14	-	nC	
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	11	-	nC
$Q_{GS}$	gate-source charge	$I_D = 15 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	3.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	2.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.7	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 15 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	4.8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.7	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	645	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	63	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	43	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 3.3 \Omega; V_{GS} = 10 \text{ V};$	-	10	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		_	5	_	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	45	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	74	-	nC

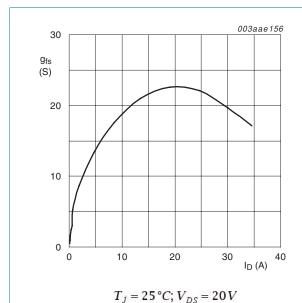


Fig 5. Forward transconductance as a function of drain current; typical values

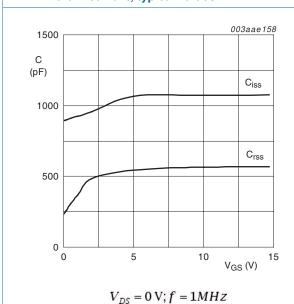
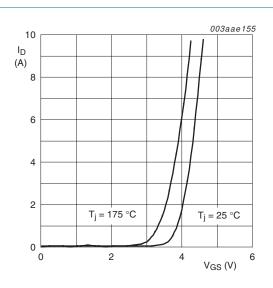
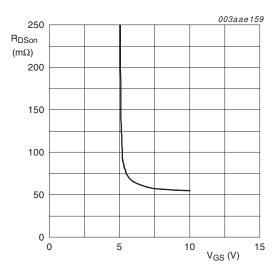


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; I_D = 15A$ 

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

PSMN069-100YS

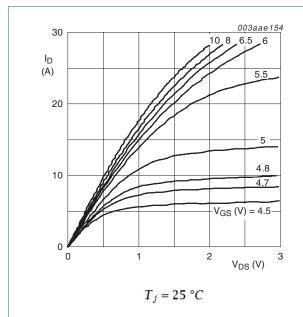


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

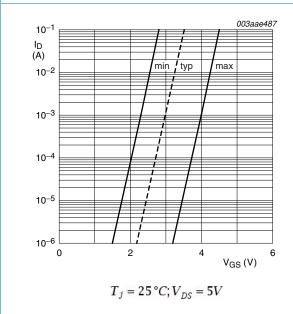
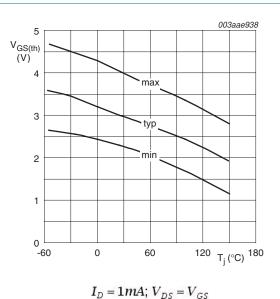


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D - I_{BL}$ ,  $V_{DS} - V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

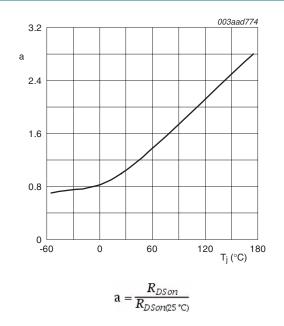
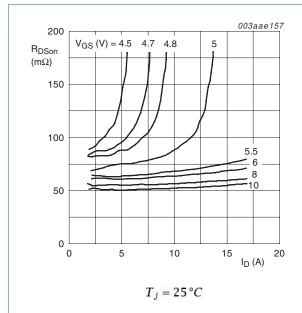


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V<sub>DS</sub>

V<sub>GS(pl)</sub>

V<sub>GS(th)</sub>

V<sub>GS</sub>

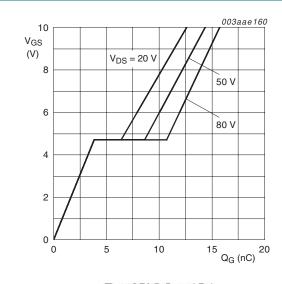
Q<sub>GS1</sub> Q<sub>GS2</sub>

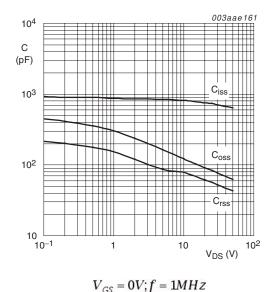
Q<sub>GG</sub>
Q<sub>G(tot)</sub>

003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25^{\circ}C; I_D = 15A$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical



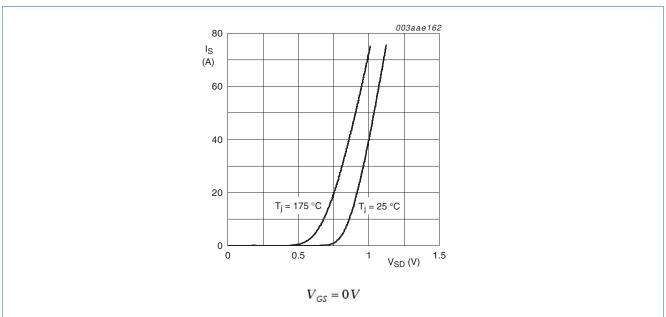


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline

# Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 

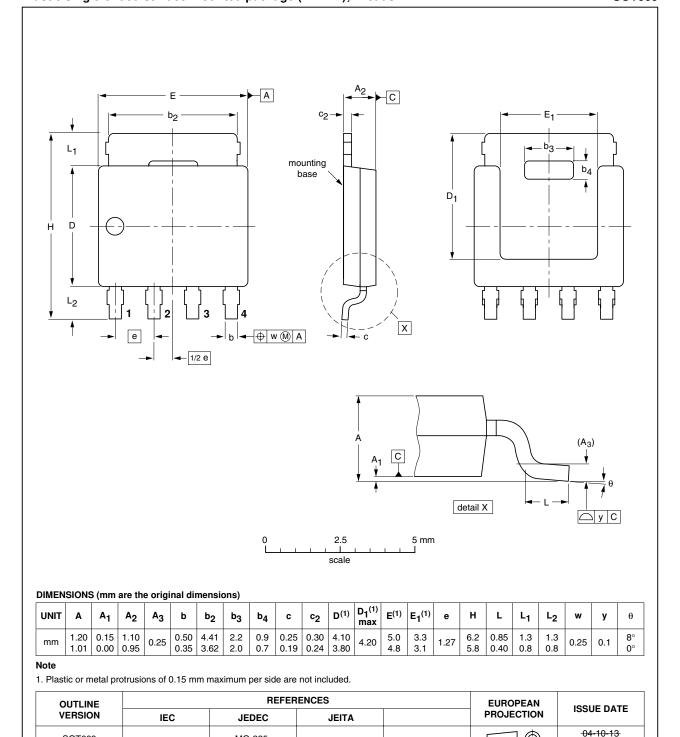


Fig 18. Package outline SOT669 (LFPAK)

PSMN069-100YS

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MO-235

06-03-16

SOT669

# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN069-100YS v.2	20101025	Product data sheet	-	PSMN069-100YS v.1
Modifications:	<ul><li>Status changed from objective to product</li><li>Various changes to content.</li></ul>			
PSMN069-100YS v.1	20100831	Objective data sheet	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PSMN069-100YS**

N-channel LFPAK 100 V 72.4 mΩ standard level MOSFET

# 11. Contents

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